

Applications

- IEEE802.11b DSSS WLAN
- IEEE802.11g,n OFDM WLAN
- High Power Wireless Networking Products

Features

- Dual Mode IEEE802.11b, IEEE802.11g, IEEE802.11n
- 23 dBm, EVM = 3%, 802.11g, OFDM 54 Mbps
- 26 dBm, ACPR < -32 dBc, 802.11b
- Integrated PA, Input Match, 2.8V reference voltage generator
- Integrated Temperature Compensated, Positive Slope Power Detector
- Pb-free, RoHS compliant and Halogen-free
- 3 mm x 3 mm x 0.6 mm QFN, MSL 3

Ordering Information

Part No.	Package	Remark
SE2565T	16 pin QFN	Samples
SE2565T-R	16 pin QFN	Tape & Reel
SE2565T-EK1	N/A	Evaluation kit

Product Description

The SE2565T is a high power 802.11bgn WLAN power amplifier module providing the functionality of the power amplifier, power detector, reference voltage generator and input match.

SE2565T

The SE2565T is designed for ease of use and maximum flexibility, with an integrated input match, and external output match to adjust the load line for either 3.3V, 23dBm operation.

The SE2565T includes a temperature compensated transmit power detector with over 20 dB of dynamic range and <1.2dB variation under 3:1 mismatch at the antenna.

The SE2565T includes a digital enable control due to an integrated reference voltage generator. The power ramp rise/fall time is $0.5 \mu s$ typical.

Functional Block Diagram

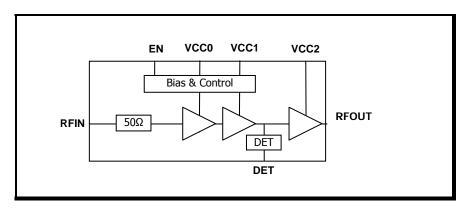


Figure 1: Functional Block Diagram



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Product Preview

The datasheet contains information from the product concept specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Preliminary Information

The datasheet contains information from the design target specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Production testing may not include testing of all parameters.

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